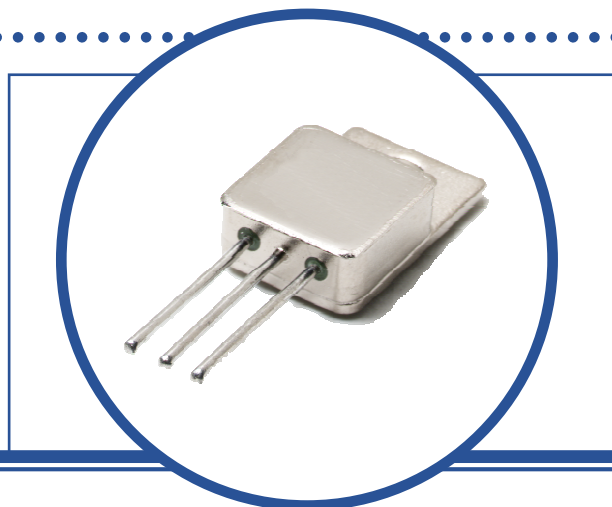


SILICON CARBIDE (SiC) SCHOTTKY DIODE

SML10SIC06YC

- Hermetic Metal TO-257AA Package.
- Semelab's Silicon Carbide (SiC) Schottky diodes exhibit low forward voltage and superb high temperature performance.
- Suitable for high-frequency hard switching applications, where system efficiency and reliability are paramount.
- No reverse recovery time due to absence of minority carrier injection.
- Screening Options Available.



ABSOLUTE MAXIMUM RATINGS (Per Diode, $T_C = 25^\circ\text{C}$ unless otherwise stated)

V_R	DC Reverse Voltage	600V
V_{RRM}	Repetitive Peak Reverse Voltage	600V
I_F	DC Forward Current ($T_J = 175^\circ\text{C}$)	10A
I_{FRM}	Repetitive Peak Forward Current ⁽¹⁾	67A
I_{FSM}	Surge Peak Forward Current ⁽²⁾	250A
P_D	Total Power Dissipation at Derate Above 25°C	100W 0.5W/ $^\circ\text{C}$
T_J	Junction Temperature Range	-55 to $+225^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to $+225^\circ\text{C}$

THERMAL PROPERTIES

Symbols	Parameters	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction To Case	2.0	$^\circ\text{C}/\text{W}$

Notes

(1) $T_c = 25^\circ\text{C}$, $T_p = 10\text{ms}$, Half Sine Wave, $D = 0.3$

(2) $T_c = 25^\circ\text{C}$, $T_p = 10\mu\text{s}$

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ELECTRICAL CHARACTERISTICS (Per Diode, $T_C = 25^\circ\text{C}$ unless otherwise stated)

Static Characteristics

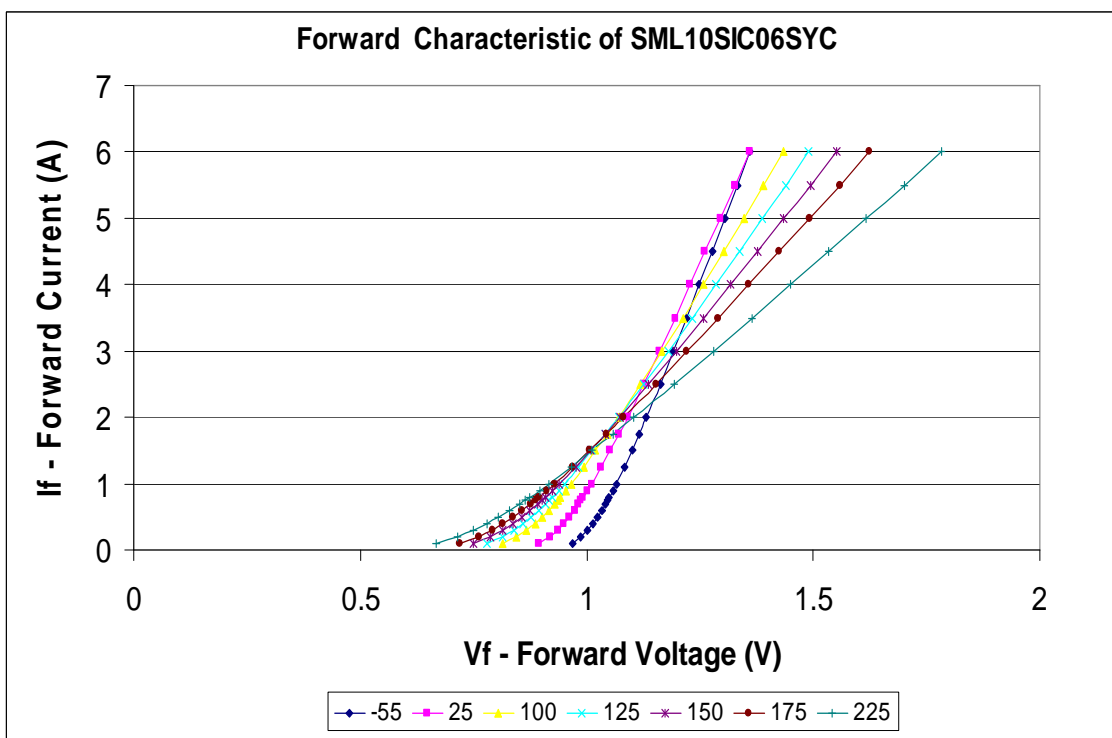
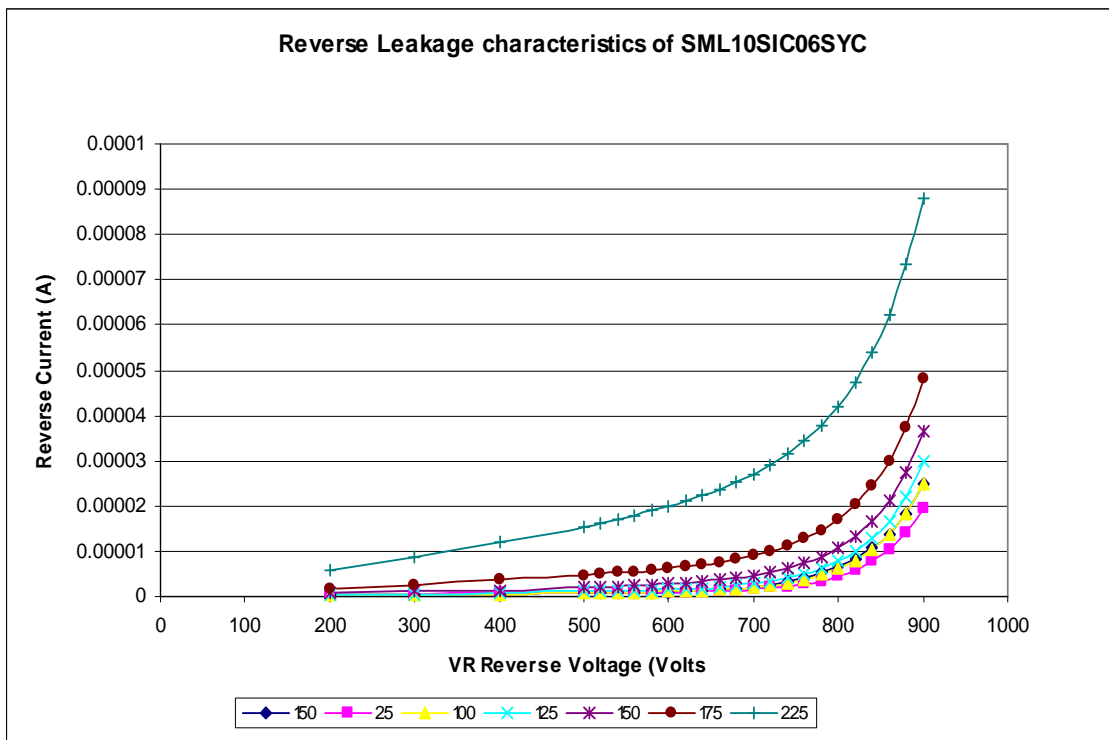
Symbols	Parameters	Test Conditions	Min.	Typ.	Max.	Units
V_F	Forward Voltage	$I_F = 10\text{A}$		1.5	1.8	V
		$T_J = 175^\circ\text{C}$		2.0	2.4	
I_R	Reverse Current	$V_R = 600\text{V}$		10	50	μA
		$T_J = 175^\circ\text{C}$		20	200	

Dynamic Characteristics

Q_C	Total Capacitive Charge	$V_R = 600\text{V}$, $I_F = 10\text{A}$ $\delta i/\delta t = 500\text{A}/\mu\text{s}$		25		nC
C	Total Capacitance	$V_R = 1.0\text{V}$, $f = 1.0\text{MHz}$		480		pF
		$V_R = 200\text{V}$, $f = 1.0\text{MHz}$		50		
		$V_R = 400\text{V}$, $f = 1.0\text{MHz}$		42		

SILICON CARBIDE (SiC) SCHOTTKY DIODE SML10SIC06YC

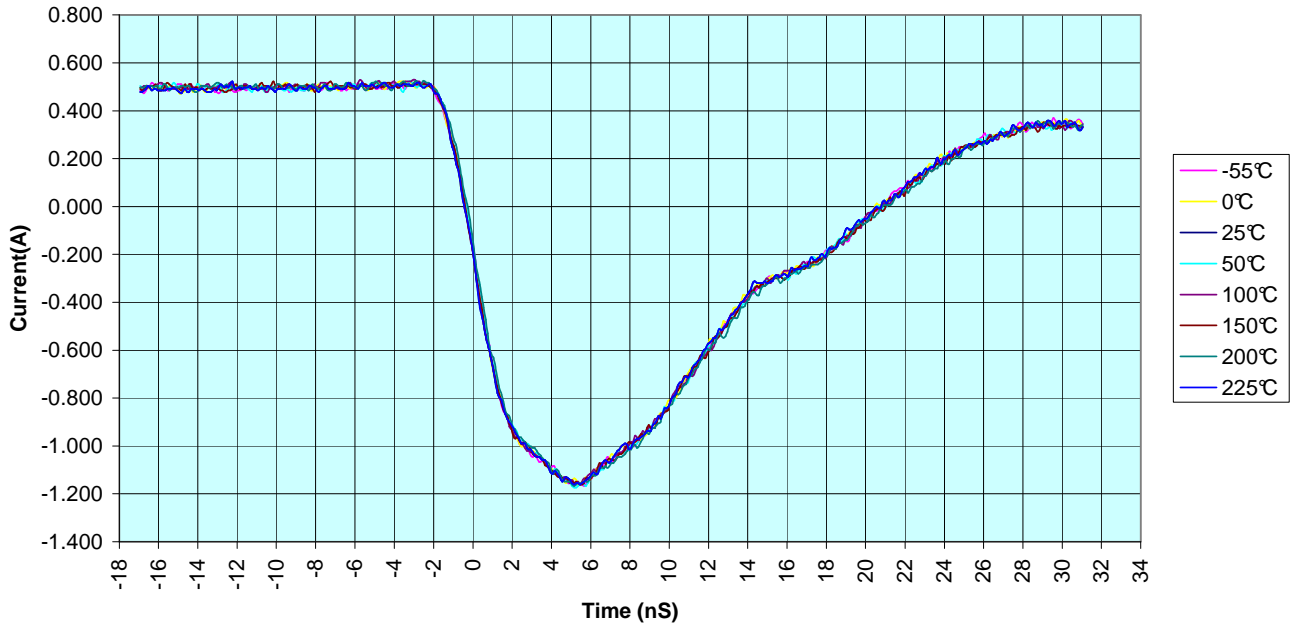
Typical Performance Over Temperature Range



SILICON CARBIDE (SiC) SCHOTTKY DIODE SML10SIC06YC

SiC Schottky Diode, no minority carrier recombination thus zero reverse recovery. Recovery time shown is due to a small junction capacitance charge and is independent of junction temperature

SML10SIC06YC
Equivalent Reverse Recovery Time Device
 $I_F=500\text{mA}$, $I_R = 1\text{A}$, $I_{RR}=250\text{mA}$



MECHANICAL DATA

Dimensions in mm (inches)

